AMENDMENTS TO THE CLAIMS

Claims 1-5 (Canceled).

6. (Currently Amended) A pad structure for a liquid crystal display including a grinding area adjacent to an edge portion of a lower substrate of the liquid crystal display, a pad contact area and an anisotropic conductive film deposit area, the pad structure comprising:

a tape carrier package layer to receive a driving signal;

an anisotropic conductive film formed on a lower portion of the tape carrier package layer and covering at least the pad contact area of the liquid crystal display;

an insulating film defining a plurality of contact holes therethrough, the insulating film disposed on a lower portion of the anisotropic conductive film in the pad contact area of the liquid crystal dispay;

a plurality of gate and data pads; and

a transparent conductive layer electrically connecting the gate and data pads to the anisotropic conductive film through the contact holes,

wherein the entire upper, side, and end surfaces of the gate and data pads are completely covered by the <u>insulating</u> insulting film and the anisotropic conductive film conductive layer, and

wherein the pad contact area is separated from the grinding area by a predetermined interval.

- 7. (Original) The pad structure according to claim 6, wherein the insulating film is formed on side surfaces and upper parts of the gate and data pads.
- 8. (Original) The pad structure according to claim 7, wherein the gate and data pads are formed on a substrate, and the insulating film contacts the substrate at end portions of the gate pads and data pads.
- 9. (Original) The pad structure according to claim 6, wherein a gate insulating film is formed between the gate and data pads.

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Claims 10-18 (Canceled).

19. (Currently Amended) A pad structure for a liquid crystal display including a grinding area adjacent to an edge portion of a lower substrate of the liquid crystal display and a pad contact area, comprising:

a substrate;

at least one input pad formed on the substrate;

an insulating film formed on the pad contact area of the <u>input</u> pad but absent from the grinding area, the insulating film entirely covering the side and end surfaces of the <u>input</u> pad and a portion of the substrate adjacent to the side surfaces of the <u>input</u> pad; and

at least one conductive layer connected to the <u>input</u> pad through contact holes defined through the insulating film, wherein the <u>input</u> pad is separated from the grinding area by a predetermined interval <u>and the at least one conductive layer is absent from the grinding area.</u>

20. (Currently Amended) A liquid crystal display formed on a substrate, comprising:

an active region defined at a first portin of the substrate;

a grinding area defined at a second portion of the substrate, wherein the grinding area is adjacent to an edge poriton of the substrate; and

a pad contact area defined on a third portion of the substrate between and adjacent to each of the active region and the grinding area, the pad contact area including:

at least input one pad formed on the substrate;

an insulating film formed on the input pad,

at least one conductive layer connected to the <u>input</u> pad through contact holes defined through the insulating film,

wherein the insulating film covers the entire side and end surfaces of the <u>input</u> pad and a portion of the substrate adjacent to the side and end surfaces of the <u>input</u> pad such that the insulating film and the at least one conductive layer [[are]] is absent in the grinding region, and

wherein the <u>input</u> pad is seprated from the grinding area by a predetermined interval.

- 21. (New) The pad structure according to claim 6, wherein the conductive layer is indium tin oxide and the conductive layer is completely covered by the anisotropic conductive film.
- 22. (New) The pad structure according to claim 19, wherein the at least one conductive layer is indium tin oxide.
- 23. (New) The liquid crystal display according to claim 20, wherein the at least one conductive layer is indium tin oxide.